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## Metal-Guided Selective Growth of 2D Materials: Demonstration of a Bottom-Up CMOS Inverter

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#	Paper	IF	Citations
31	Synergistic additive-mediated CVD growth and chemical modification of 2D materials. <i>Chemical Society Reviews</i> , <b>2019</b> , 48, 4639-4654	58.5	66
30	Direct Epitaxial Synthesis of Selective Two-Dimensional Lateral Heterostructures. <i>ACS Nano</i> , <b>2019</b> , 13, 13047-13055	16.7	28
29	Recent progress in devices and circuits based on wafer-scale transition metal dichalcogenides. <i>Science China Information Sciences</i> , <b>2019</b> , 62, 1	3.4	12
28	Second-harmonic generation of structured light by transition-metal dichalcogenide metasurfaces. <i>Physical Review A</i> , <b>2020</b> , 102,	2.6	2
27	Ultrabroadband Tuning and Fine Structure of Emission Spectra in Lanthanide Er-Doped ZnSe Nanosheets for Display and Temperature Sensing. <i>ACS Nano</i> , <b>2020</b> , 14, 16003-16012	16.7	22
26	Wafer-Scale Organic Complementary Inverters Fabricated with Self-Assembled Monolayer Field-Effect Transistors. <i>Advanced Electronic Materials</i> , <b>2020</b> , 6, 2000515	6.4	4
25	Epitaxial Growth and Determination of Band Alignment of Bi <sub>2</sub> Te <sub>3</sub> /WSe <sub>2</sub> Vertical van der Waals Heterojunctions. <b>2020</b> , 2, 1351-1359		5
24	Analogue two-dimensional semiconductor electronics. <i>Nature Electronics</i> , <b>2020</b> , 3, 486-491	28.4	31
23	WSe <sub>2</sub> 2D p-type semiconductor-based electronic devices for information technology: Design, preparation, and applications. <i>Information Materials</i> , <b>2020</b> , 2, 656-697	23.1	49
22	Vertical Chemical Vapor Deposition Growth of Highly Uniform 2D Transition Metal Dichalcogenides. <i>ACS Nano</i> , <b>2020</b> , 14, 4646-4653	16.7	49
21	Recent progresses of NMOS and CMOS logic functions based on two-dimensional semiconductors. <i>Nano Research</i> , <b>2021</b> , 14, 1768-1783	10	8
20	Electronics based on two-dimensional materials: Status and outlook. <i>Nano Research</i> , <b>2021</b> , 14, 1752-1767	10	21
19	Strain-Directed Layer-By-Layer Epitaxy Toward van der Waals Homo- and Heterostructures. <b>2021</b> , 3, 442-453		3
18	2D MoS <sub>2</sub> Charge Injection Memory Transistors Utilizing Hetero-Stack SiO <sub>2</sub> /HfO <sub>2</sub> Dielectrics and Oxide Interface Traps. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2100074	6.4	0
17	Fermi-Level Pinning Free High-Performance 2D CMOS Inverter Fabricated with Van Der Waals Bottom Contacts. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2001212	6.4	11
16	A SPICE Compact Model for Ambipolar 2-D-Material FETs Aiming at Circuit Design. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 68, 3096-3103	2.9	0
15	High-performance n-type transistors based on CVD-grown large-domain trilayer WSe <sub>2</sub> . <i>APL Materials</i> , <b>2021</b> , 9, 071109	5.7	1

14	Large-Scale Uniform-Patterned Arrays of Ultrathin All-2D Vertical Stacked Photodetector Devices. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 34696-34704	9.5	2
13	Polarity Control and Weak Fermi-Level Pinning in PdSe Transistors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 43480-43488	9.5	5
12	Growth Mechanisms and Morphology Engineering of Atomic Layer-Deposited WS. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 43115-43122	9.5	2
11	Design and tailoring of two-dimensional Schottky, PN and tunnelling junctions for electronics and optoelectronics. <i>Nanoscale</i> , <b>2021</b> , 13, 6713-6751	7.7	13
10	Substitutionally Doped MoSe for High-Performance Electronics and Optoelectronics. <i>Small</i> , <b>2021</b> , 17, e2102855	11	3
9	Compact I-V Model for Ambipolar Field-Effect Transistors With 2D Transition Metal Dichalcogenide as Semiconductor. <i>IEEE Nanotechnology Magazine</i> , <b>2020</b> , 19, 841-848	2.6	0
8	Recent progress in the CVD growth of 2D vertical heterostructures based on transition-metal dichalcogenides. <i>CrystEngComm</i> ,	3.3	1
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5	A perspective on high-entropy two-dimensional materials. <i>SusMat</i> , <b>2022</b> , 2, 65-75		0
4	Utilizing trapped charge at bilayer 2D MoS <sub>2</sub> /SiO <sub>2</sub> interface for memory applications.. <i>Nanotechnology</i> , <b>2022</b> ,	3.4	0
3	Ambipolar Nonvolatile Memory Behavior and Reversible Type-Conversion in MoSe <sub>2</sub> /MoSe <sub>2</sub> Transistors with Modified Stack Interface. 2205567		0
2	Epitaxial van der Waals contacts for low schottky barrier MoS <sub>2</sub> field effect transistors.		0
1	Integrated Low-Dimensional Semiconductors for Scalable Low-power CMOS Logic.		0